



## Precision Monolithic Quad SPST CMOS Analog Switches

### DESCRIPTION

The DG1411, DG1412, DG1413 are ± 15 V precision monolithic quad single-pole single-throw (SPST) CMOS analog switches. Built on a new CMOS process, the Vishay Siliconix DG1411, DG1412, and DG1413 offer low on-resistance of 1.5 Ω. The low and flat resistance over the full signal range ensures excellent linearity and low signal distortion. The new CMOS platform provides low power dissipation, minimized parasitic capacitance, and low charge injection.

The devices operate from either a single 4.5 V to 24 V power supply, or from dual ± 4.5 V to ± 15 V power supplies. The analog switches don't require a V<sub>L</sub> logic supply, while all digital inputs have 0.8 V and 2 V logic thresholds to ensure low-voltage TTL / CMOS compatibility.

The DG1411, DG1412, and DG1413 are bi-directional and support analog signals up to the supply voltage when on, and block them when off. The devices each feature four independently selectable SPST switches. The DG1411 is normally closed, while the DG1412 is normally open. The DG1413 has two normally open and two normally closed switches with guaranteed break-before-make operation.

Combined with fast 100 ns switching times, the improved performance of the DG1411, DG1412, and DG1413 make the devices ideal for signal switching and relay replacement in data acquisition, industrial control and automation, communication, and A/V systems, in addition to medical instrumentation and automated test equipment.

The switches are available in RoHS-compliant, halogen-free TSSOP16 and QFN16 4 mm by 4 mm packages.

### FEATURES

- 35 V supply max. rating
- On-resistance: 1.5 Ω
- On-resistance flatness: 0.3 Ω
- Channel to channel ON-resistance match: 0.1 Ω
- Supports single and dual supply operation
- Fully specified at ± 15 V, ± 5 V, and +12 V
- Integrated V<sub>L</sub> supply
- 3 V logic compatible
- Low parasitic capacitance: C<sub>S(OFF)</sub>: 11 pF, C<sub>D(ON)</sub>: 87 pF
- Rail to rail signal handling
- Material categorization: For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

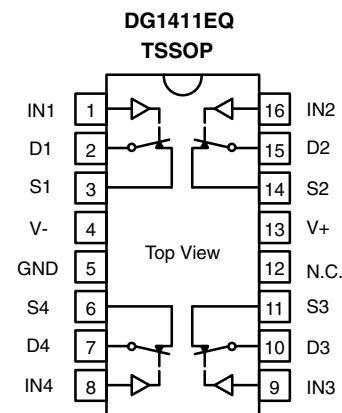
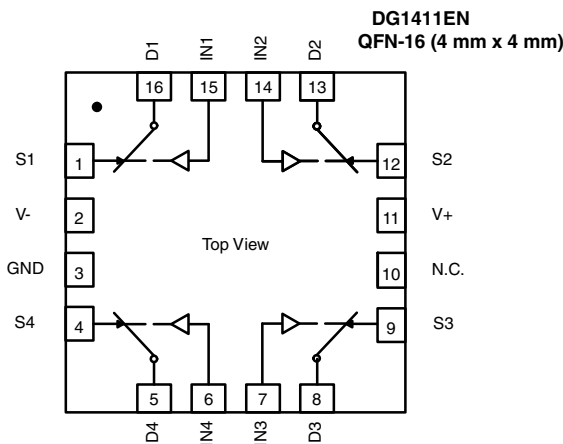
### BENEFITS

- Low insertion loss
- Low distortion
- Break-before-make switching
- Low charge injection over the full signal range

### APPLICATIONS

- Medical and Healthcare equipment
- Data acquisition system
- Industrial control and automation
- Test and measurement equipment
- Communication systems
- Battery powered systems
- Sample and hold circuits
- Audio and video signal switching
- Relay replacement

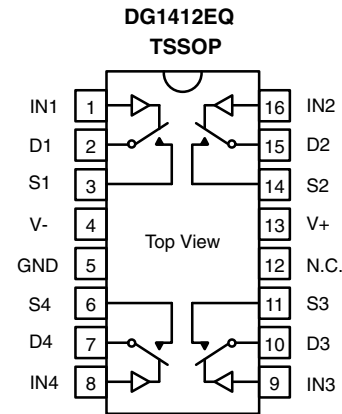
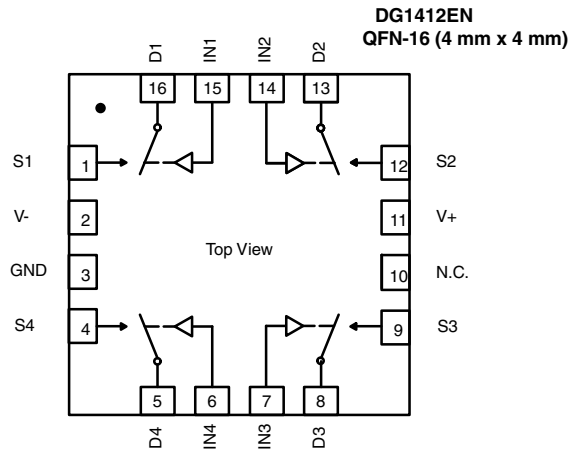
### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION - DG1411



TRUTH TABLE - DG1411	
LOGIC	SWITCH
0	On
1	Off

### Notes

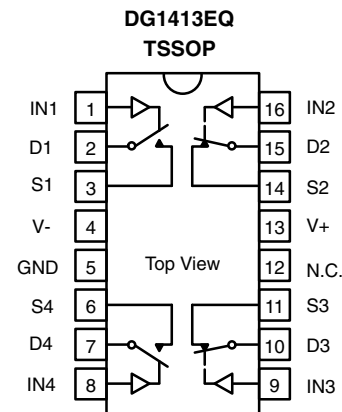
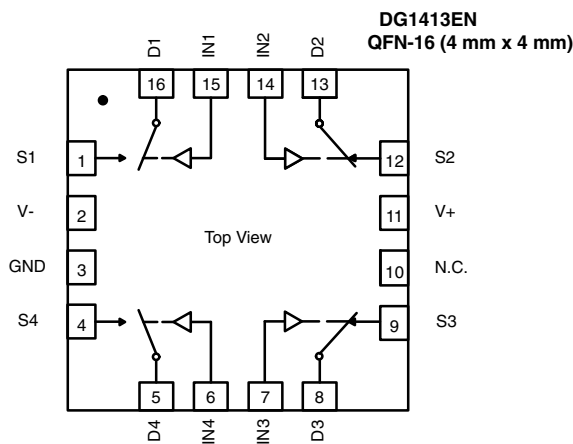
- QFN EXPOSED PAD TIED TO V-
- N.C. = NO CONNECT
- Switches Shown for Logic "0" Input

**FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION - DG1412**


TRUTH TABLE - DG1412	
LOGIC	SWITCH
0	Off
1	On

**Notes**

- QFN EXPOSED PAD TIED TO V-
- N.C. = NO CONNECT
- Switches Shown for Logic "0" Input

**FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION - DG1413**


TRUTH TABLE - DG1413		
LOGIC	SWITCHES 1, 4	SWITCHES 2, 3
0	Off	On
1	On	Off

**Notes**

- QFN EXPOSED PAD TIED TO V-
- N.C. = NO CONNECT
- Switches Shown for Logic "0" Input



DEVICE OPTIONS				
PART NUMBER	CONFIGURATION	SWITCH FUNCTION	TEMPERATURE RANGE	PACKAGE
DG1411EN-T1-GE4	Quad SPST	NC	-40 °C to +125 °C	QFN (4 mm x 4 mm) 16L (Variation 2)
DG1412EN-T1-GE4	Quad SPST	NO	-40 °C to +125 °C	QFN (4 mm x 4 mm) 16L (Variation 2)
DG1413EN-T1-GE4	Quad SPST	NC/NO	-40 °C to +125 °C	QFN (4 mm x 4 mm) 16L (Variation 2)
DG1411EQ-T1-GE3	Quad SPST	NC	-40 °C to +125 °C	TSSOP-16
DG1412EQ-T1-GE3	Quad SPST	NO	-40 °C to +125 °C	TSSOP-16
DG1413EQ-T1-GE3	Quad SPST	NC/NO	-40 °C to +125 °C	TSSOP-16

ABSOLUTE MAXIMUM RATINGS			
ELECTRICAL PARAMETER	CONDITIONS	LIMITS	UNIT
V+	Reference to GND	-0.3 V to +25 V	V
V-	Reference to GND	+0.3 V to -25 V	
V+ to V-		+35	
Analog Inputs (S or D)		V- (-0.3 V) to V+ (+0.3 V)	
Digital Inputs		GND (-0.3 V) to V+ (+0.3 V)	
Maximum Continuous Switch Current	TSSOP-16, T <sub>A</sub> = 25 °C	190	mA
	QFN (4 mm x 4 mm) 16L, T <sub>A</sub> = 25 °C	250	
	TSSOP-16, T <sub>A</sub> = 125 °C	90	
	QFN (4 mm x 4 mm) 16L, T <sub>A</sub> = 125 °C	100	
Maximum Pulse Switch Current	Pulse at 1 mS, 10 % duty cycle	500	
Thermal Resistance	TSSOP-16	130	°C/W
	QFN (4 mm x 4 mm) 16L	32	
Temperature			
Operating Temperature		-40 to 125	°C
Max. Operating Junction Temperature		150	
Operating Junction Temperature		125	
Storage Temperature		-65 to 150	

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING RANGE			
ELECTRICAL	MINIMUM	MAXIMUM	UNIT
IN	± 4.5	± 16.5	V



ELECTRICAL CHARACTERISTICS							
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V+ = 15 V, V- = -15 V VINH = 2 V, VINL = 0.8 V	+25 °C	-40 °C to +85 °C	-40 °C to +125 °C	TYP./MAX.	UNIT
<b>Analog Switch</b>							
Analog Signal Range	V <sub>ANALOG</sub>		V- to V+			-	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>S</sub> = ± 10 V, I <sub>S</sub> = -10 mA; see fig. 23 V+ = +13.5 V, V- = -13.5 V	1.5	-	-	Typ.	Ω
			1.8	2.3	2.6	Max.	
ON-Resistance Flatness	R <sub>flat(on)</sub>	V <sub>S</sub> = ± 10 V, I <sub>S</sub> = -10 mA	0.3	-	-	-	Ω
			0.36	0.45	0.48	Max.	
ON-Resistance Matching	ΔR <sub>DS(on)</sub>		0.08	-	-	Typ.	Ω
			0.18	0.19	0.21	Max.	
Switch Off Leakage Current	I <sub>S</sub> /I <sub>d(off)</sub>	V+ = +16.5 V, V- = -16.5 V V <sub>S</sub> = ± 10 V, V <sub>D</sub> = ± 10 V; see fig. 24	± 0.03	-	-	Typ.	nA
			± 0.55	± 2	± 12.5	Max.	
Channel On Leakage Current	I <sub>d(on)</sub>	V <sub>S</sub> = V <sub>D</sub> = ± 10 V; see fig. 25	± 0.15	-	-	Typ.	nA
			± 2	± 4	± 35	Max.	
<b>Digital Control</b>							
Input, High Voltage	V <sub>INH</sub>		-	-	2	V <sub>min.</sub>	V
Input, Low Voltage	V <sub>INL</sub>		-	-	0.8	V <sub>max.</sub>	
Input Leakage	I <sub>IN</sub>	V <sub>IN</sub> = V <sub>GND</sub> or V+	0.005	-	-	Typ.	μA
			-	-	± 0.1	Max.	
Digital Input Capacitance	C <sub>IN</sub>		3.5	-	-	Typ.	pF
<b>Dynamic Characteristics</b>							
Break-Before-Make Time	t <sub>OPEN</sub>	V <sub>S1</sub> = V <sub>S2</sub> = 10 V, see fig. 31; R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF	36	-	-	Typ.	ns
			-	-	10	Min.	
Turn-On Time	t <sub>ON</sub>	V <sub>S</sub> = 10 V, see fig. 30 R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF	100	-	-	Typ.	ns
			150	170	190	Max.	
Turn-Off Time	t <sub>OFF</sub>		64	-	-	Typ.	ns
			120	140	160	Max.	
Charge Injection	Q <sub>INj</sub>	C <sub>L</sub> = 1 nF, R <sub>GEN</sub> = 0 Ω, V <sub>S</sub> = 0 V see fig. 32	-20	-	-	Typ.	pC
Off Isolation	OIRR	C <sub>L</sub> = 5 pF, R <sub>L</sub> = 50 Ω, 100 kHz	-80	-	-	Typ.	dB
Cross Talk	X <sub>TALK</sub>	C <sub>L</sub> = 5 pF, R <sub>L</sub> = 50 Ω, 1 MHz	-100	-	-	Typ.	
Insertion Loss		f = 1 MHz, R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF	-0.08	-	-	Typ.	
Total Harmonic Distortion	THD	R <sub>L</sub> = 110 Ω, 15 V <sub>p-p</sub> , f = 20 Hz to 20 kHz	0.014	-	-	Typ.	%
Bandwidth, -3dB	BW	C <sub>L</sub> = 5 pF, R <sub>L</sub> = 50 Ω	210	-	-	Typ.	MHz
Source Off Capacitance	C <sub>S(off)</sub>	f = 1 MHz, V <sub>S</sub> = 0 V	11	-	-	Typ.	pF
Drain Off Capacitance	C <sub>D(off)</sub>		24	-	-	Typ.	
Drain On Capacitance	C <sub>D(on)</sub>		87	-	-	Typ.	
<b>Power Requirements</b>							
Power Supply Range		GND = 0 V	± 4.5/± 16.5 min./max.				V
Power Supply Current	I+	Digital Inputs 0 or V+ V+ = +16.5 V, V- = -16.5 V	0.001	-	-	Typ.	μA
			-	-	1	Max.	
			220	-	-	Typ.	
	-	-	380	Max.			
	I-	Digital Inputs 0 or V+	0.001	-	-	Typ.	
			-	-	1	Max.	



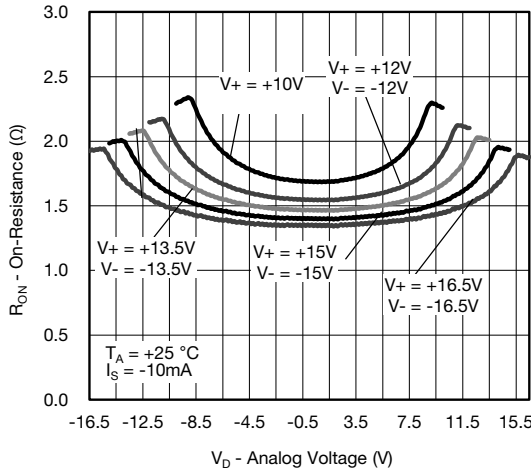
ELECTRICAL CHARACTERISTICS - SINGLE 12 V SUPPLY								
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V <sub>+</sub> = 12 V, V <sub>-</sub> = 0 V V <sub>INH</sub> = 2 V, V <sub>INL</sub> = 0.8 V	+25 °C	-40 °C to +85 °C	-40 °C to +125 °C	TYP./MAX.	UNIT	
<b>Analog Switch</b>								
Analog Signal Range	V <sub>ANALOG</sub>		0 V to V <sub>+</sub>				V	
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>S</sub> = 0 V to 10 V, I <sub>S</sub> = -10 mA; see fig. 23, V <sub>+</sub> = 10.8 V, V <sub>-</sub> = 0 V	2.8	-	-	Typ.	Ω	
			3.5	4.3	4.8	Max.		
ON-Resistance Flatness	R <sub>flat(on)</sub>	V <sub>S</sub> = 0 V to 10 V, I <sub>S</sub> = -10 mA	0.6	-	-	Typ.	Ω	
			1.1	1.2	1.3	Max.		
ON-Resistance Matching	ΔR <sub>on</sub>		0.08	-	-	Typ.	Ω	
			0.21	0.23	0.25	Max.		
Switch Off Leakage Current	I <sub>S</sub> /I <sub>d(off)</sub>	V <sub>+</sub> = 10.8 V, V <sub>-</sub> = 0 V V <sub>S</sub> = 1 V/10 V, V <sub>D</sub> = 10 V/0 V see fig. 24	± 0.02	-	-	Typ.	nA	
			± 0.55	± 2	± 12.5	Max.		
Channel On Leakage Current	I <sub>d(on)</sub>	V <sub>S</sub> = V <sub>D</sub> = 1 V/10 V; see fig. 25	± 0.15	-	-	Typ.	nA	
			± 1.5	± 4	± 30	Max.		
<b>Digital Control</b>								
Input, High Voltage	V <sub>INH</sub>		-	-	2	Min.	V	
Input, Low Voltage	V <sub>INL</sub>		-	-	0.8	Max.		
Input Leakage	I <sub>IN</sub>	V <sub>IN</sub> = V <sub>GND</sub> OR V <sub>+</sub>	0.001	-	-	Typ.	μA	
			-	-	± 0.1	Max.		
Digital Input Capacitance	C <sub>IN</sub>		3.5	-	-	Typ.	pF	
<b>Dynamic Characteristics</b>								
Break-Before-Make Time	t <sub>OPEN</sub>	V <sub>S1</sub> = V <sub>S2</sub> = 8 V; see fig. 31, R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF	130	-	-	Typ.	ns	
			-	-	40	Min.		
Turn-On Time	t <sub>ON</sub>	V <sub>S</sub> = 8 V; see fig. 30, R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF	210	-	-	Typ.	ns	
			250	320	360	Max.		
Turn-Off Time	t <sub>OFF</sub>		80	-	-	Typ.	ns	
			135	165	190	Max.		
Charge Injection	Q <sub>INj</sub>	C <sub>L</sub> = 1 nF, R <sub>GEN</sub> = 0 Ω, V <sub>S</sub> = 6 V see fig. 32	14	-	-	Typ.	pC	
Off Isolation	OIRR	R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF	100 kHz	-80	-	-	Typ.	dB
Cross Talk	X <sub>TALK</sub>		1 MHz	-100	-	-	Typ.	
Insertion Loss		f = 1 MHz, R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF	-0.16	-	-	Typ.		
Bandwidth, -3dB	BW	R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF	200	-	-	Typ.	MHz	
Source Off Capacitance	C <sub>S(off)</sub>	f = 1 MHz, V <sub>S</sub> = 6 V	17	-	-	Typ.	pF	
Drain Off Capacitance	C <sub>D(off)</sub>		30	-	-	Typ.		
Drain On Capacitance	C <sub>D(on)</sub>		94	-	-	Typ.		
<b>Power Requirements</b>								
Power Supply Range		GND = 0 V, V <sub>-</sub> = 0 V	± 5/± 16.5 min./max.				V	
Power Supply Current	I <sub>+</sub>	Digital Inputs 0 or V <sub>+</sub> V <sub>+</sub> = 13.2 V	0.001	-	-	Typ.	μA	
			-	-	1	Max.		
		IN1 = IN2 = IN3 = IN4 = 5 V	220	-	-	Typ.		
			-	-	380	Max.		



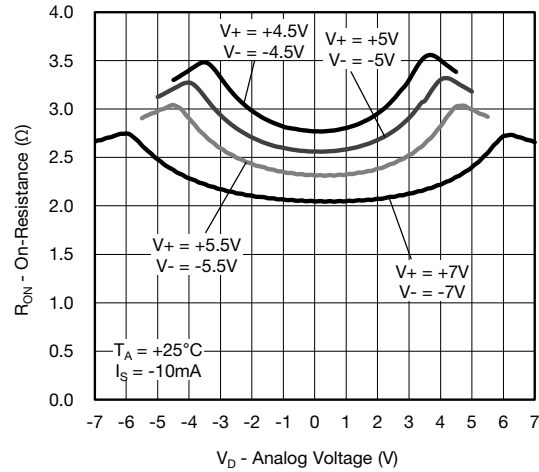
ELECTRICAL CHARACTERISTICS - DUAL ± 5 V SUPPLIES								
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V <sub>+</sub> = 5 V, V <sub>-</sub> = -5 V V <sub>INH</sub> = 2 V, V <sub>INL</sub> = 0.8 V	+25 °C	-40 °C to +85 °C	-40 °C to +125 °C	TYP./MAX.	UNIT	
<b>Analog Switch</b>								
Analog Signal Range	V <sub>ANALOG</sub>		0 to V <sub>+</sub>				V	
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>S</sub> = ± 4.5 V, I <sub>S</sub> = -10 mA; see fig. 23, V <sub>+</sub> = +4.5 V, V <sub>-</sub> = -4.5 V	3.3	-	-	Typ.	Ω	
			4	4.9	5.4	Max.		
ON-Resistance Flatness	R <sub>flat(on)</sub>	V <sub>S</sub> = ± 4.5 V, I <sub>S</sub> = -10 mA	0.9	-	-	Typ.		
			1.1	1.24	1.31	Max.		
ON-Resistance Matching	ΔR <sub>on</sub>		0.08	-	-	Typ.		
			0.22	0.23	0.25	Max.		
Switch Off Leakage Current	I <sub>S</sub> /I <sub>d(off)</sub>	V <sub>+</sub> = +5.5 V, V <sub>-</sub> = -5.5 V, V <sub>S</sub> = +/- 4.5 V, V <sub>D</sub> = +/- 4.5 V; see fig. 24	± 0.03	-	-	Typ.	nA	
			± 0.55	± 2	± 12.5	Max.		
Channel On Leakage Current	I <sub>d(on)</sub>	V <sub>S</sub> = V <sub>D</sub> = ± 4.5 V; see fig. 25	± 0.05	-	-	Typ.		
			± 1	± 4	± 30	Max.		
<b>Digital Control</b>								
Input, High Voltage	V <sub>INH</sub>		-	-	2	Min.	V	
Input, Low Voltage	V <sub>INL</sub>		-	-	0.8	Max.		
Input Leakage	I <sub>IN</sub>	V <sub>IN</sub> = V <sub>GND</sub> or V <sub>+</sub>	0.001	-	-	Typ.	μA	
			-	-	± 0.1	Max.		
Digital Input Capacitance	C <sub>IN</sub>		3.5	-	-	Typ.	pF	
<b>Dynamic Characteristics</b>								
Break-Before-Make Time	t <sub>OPEN</sub>	V <sub>S1</sub> = V <sub>S2</sub> = 3 V; see fig. 31, R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF	150	-	-	Typ.	ns	
			-	-	50	Min.		
Turn-On Time	t <sub>ON</sub>	V <sub>S</sub> = 3 V; see fig. 30, R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF	300	-	-	Typ.		
			400	465	510	Max.		
Turn-Off Time	t <sub>OFF</sub>		150	-	-	Typ.		
			290	320	380	Max.		
Charge Injection	Q <sub>INj</sub>	C <sub>L</sub> = 1 nF, R <sub>GEN</sub> = 0 Ω, V <sub>S</sub> = 0 V; see fig. 32	22	-	-	Typ.	pC	
Off Isolation	OIRR	R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF	100 KHz	-80	-	-	Typ.	dB
Cross Talk	X <sub>TALK</sub>		1 MHz	-100	-	-	Typ.	
Insertion Loss		f = 1 MHz, R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF	-0.19	-	-	Typ.		
Bandwidth, -3dB	BW	R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF	200	-	-	Typ.	MHz	
Source Off Capacitance	C <sub>S(off)</sub>	f = 1 MHz, V <sub>S</sub> = 0 V	18	-	-	Typ.	pF	
Drain Off Capacitance	C <sub>D(off)</sub>		31	-	-	Typ.		
Drain On Capacitance	C <sub>D(on)</sub>		95	-	-	Typ.		
<b>Power Requirements</b>								
Power Supply Range		GND = 0 V	± 4.5 V/± 16.5 min./max.				V	
Power Supply Current	I <sub>+</sub>	Digital Inputs 0 V or V <sub>+</sub> V <sub>+</sub> = +5.5 V, V <sub>-</sub> = -5.5 V	0.001	-	-	Typ.	μA	
			-	-	1	Max.		
	I <sub>-</sub>	Digital Inputs = 0 V or V <sub>+</sub>	0.001	-	-	Typ.		
			-	-	1	Max.		



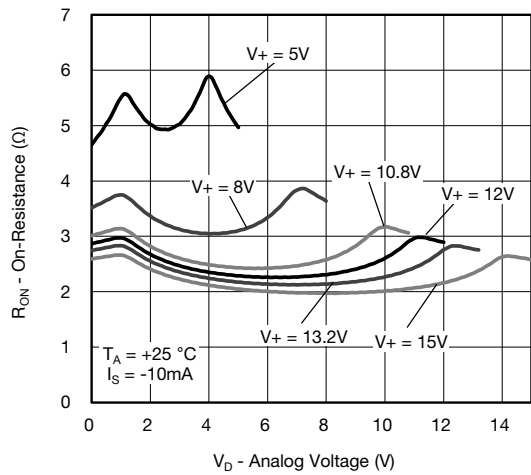
TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



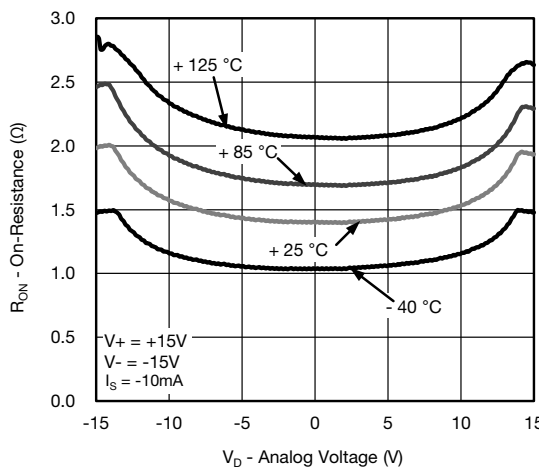
On-Resistance vs. Analog Voltage (DS1)



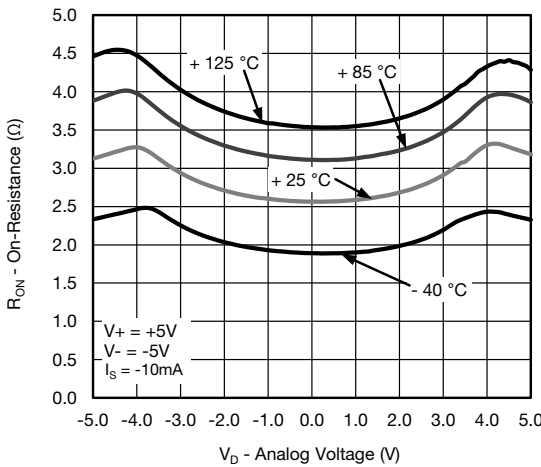
On-Resistance vs. Analog Voltage (DS2)



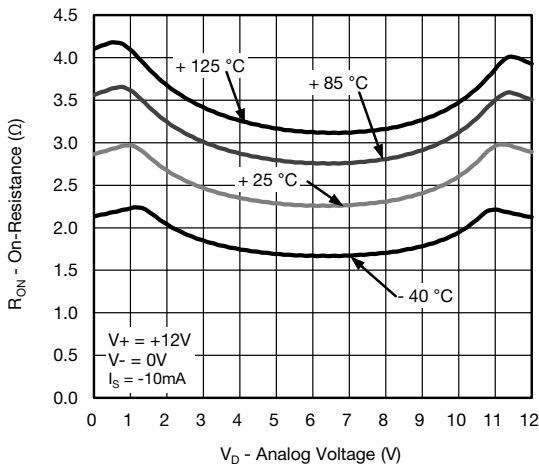
On-Resistance vs. Analog Voltage (DSS)



On-Resistance vs. Temperature (± 15 V)



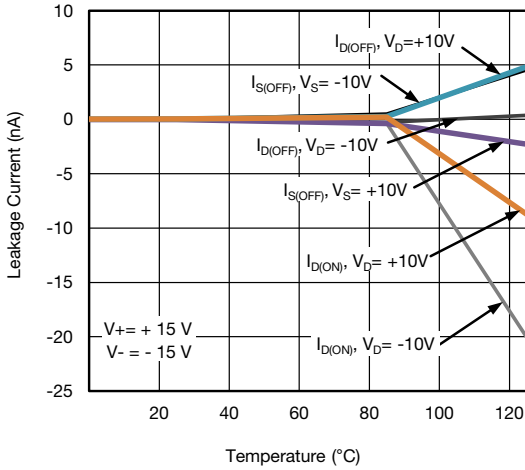
On-Resistance vs. Temperature (± 5 V)



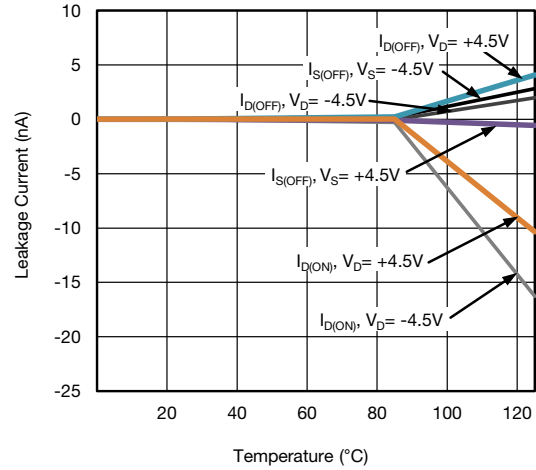
On-Resistance vs. Temperature (+12 V)



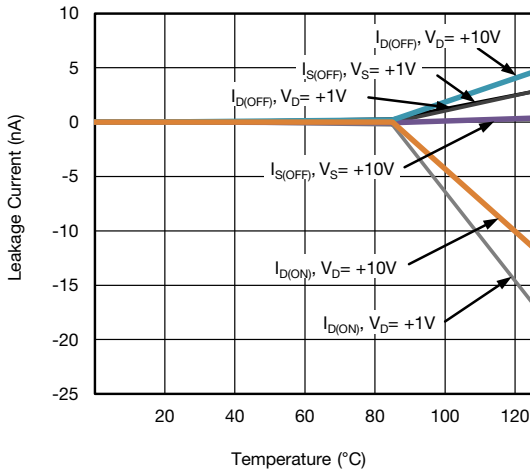
**TYPICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)



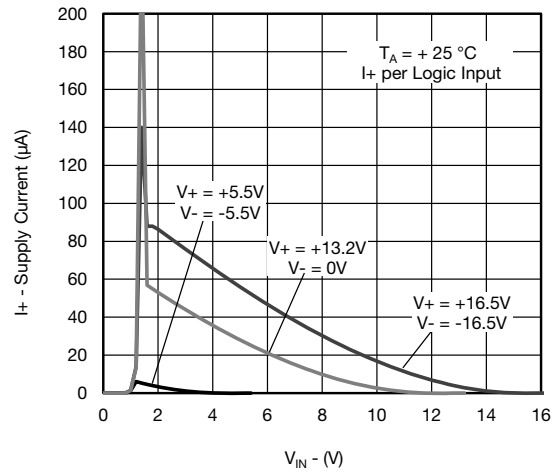
**Leakage Current vs. Temperature ( $\pm 15\text{V}$ )**



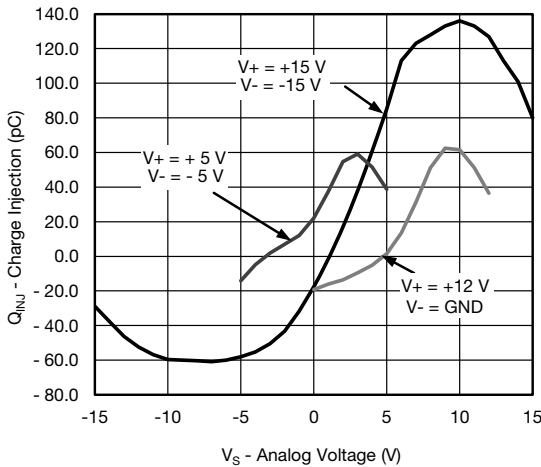
**Leakage Current vs. Temperature ( $\pm 5\text{V}$ )**



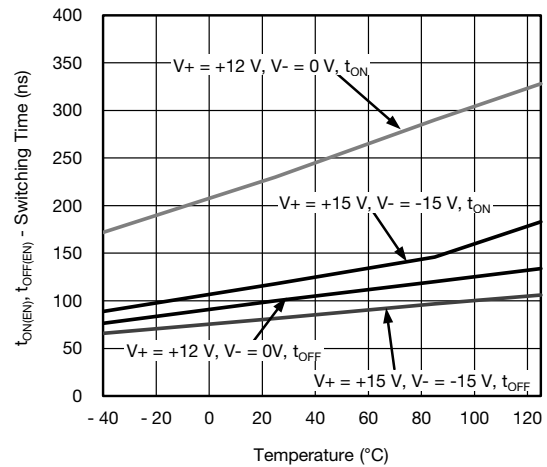
**Leakage Current vs. Temperature (+12V)**



**Supply Current vs. Logic Level**



**Charge Injection vs. Analog Voltage**

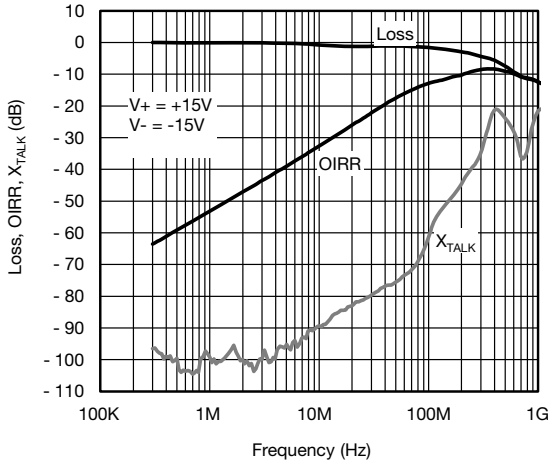


**Switching Time vs. Temperature**

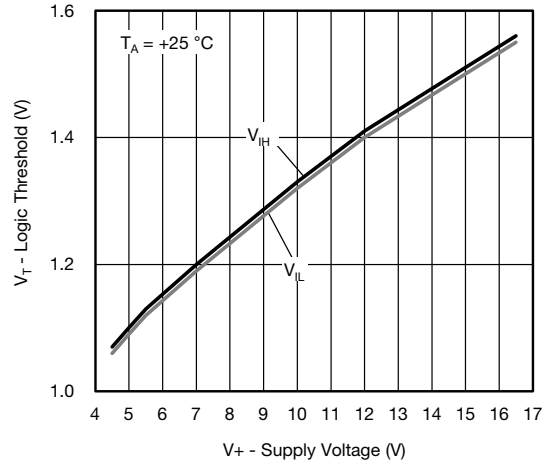




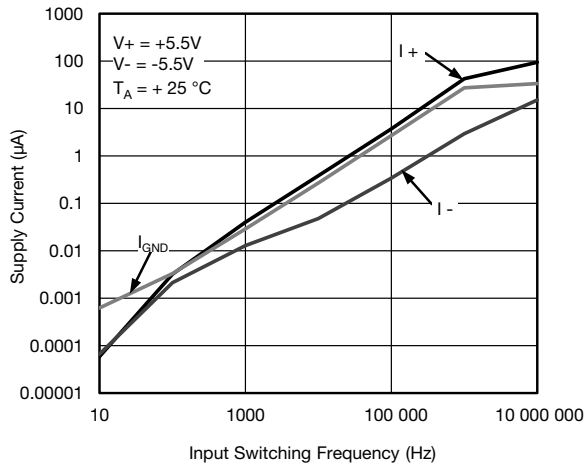
TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



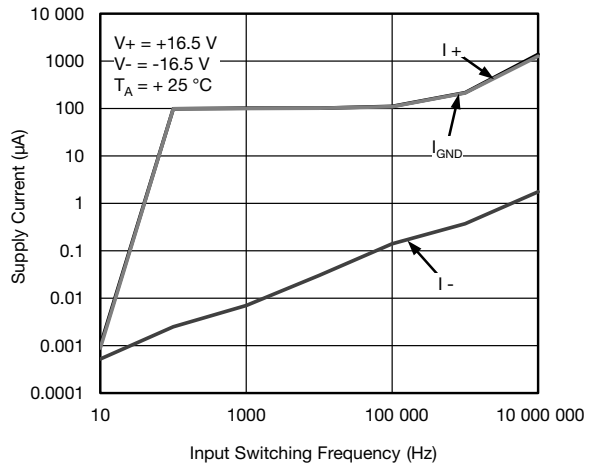
BW, OIRR, X<sub>TALK</sub> vs. Frequency



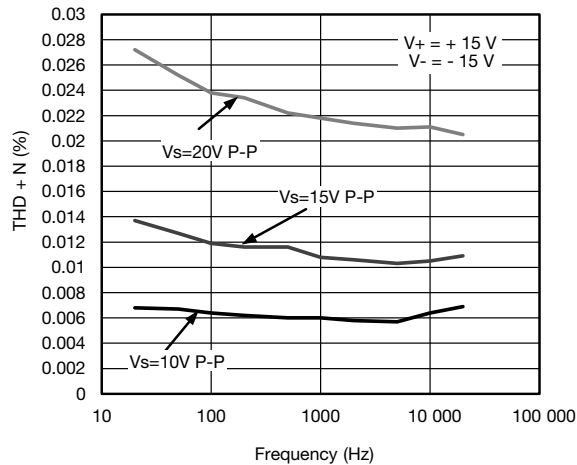
Logic Threshold vs. Supply Voltage



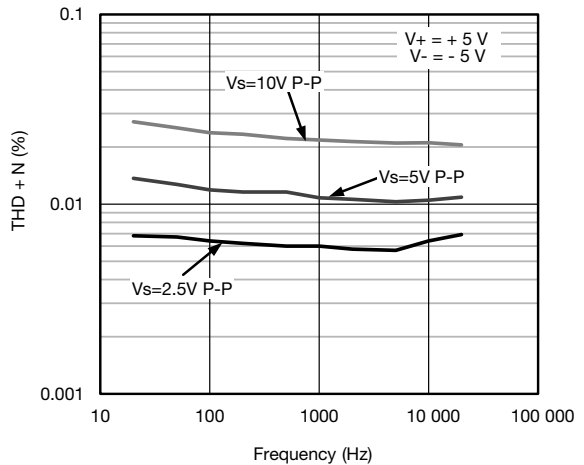
Supply Current vs. Switching Frequency (± 5.5 V)



Supply Current vs. Switching Frequency (± 16.5 V)

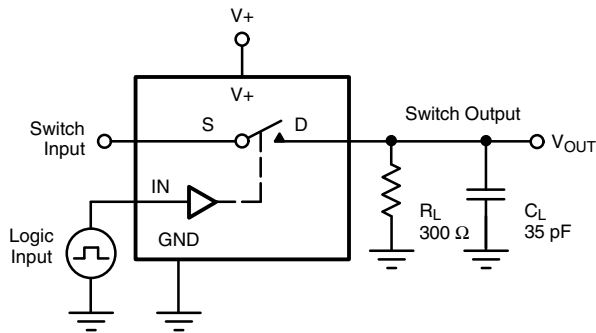


THD vs. Frequency (± 15 V)



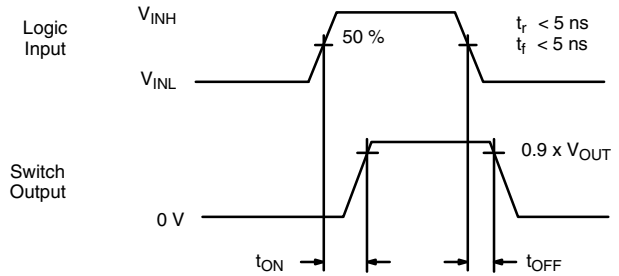
THD vs. Frequency (± 5 V)

TEST CIRCUITS



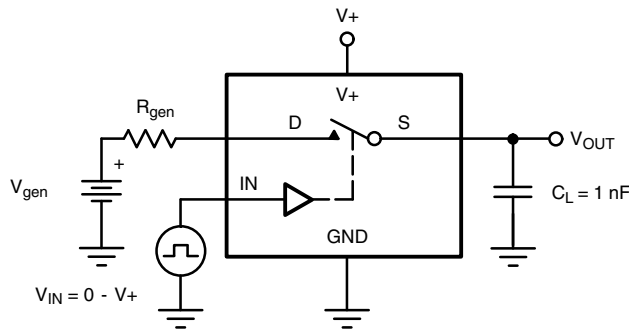
$C_L$  (includes fixture and stray capacitance)

$$V_{OUT} = V_D \left( \frac{R_L}{R_L + R_{ON}} \right)$$

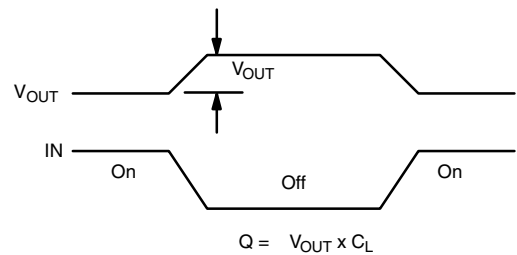


Logic "1" = Switch On  
Logic input waveforms inverted for switches that have the opposite logic sense.

Fig. 1 - Switching Time

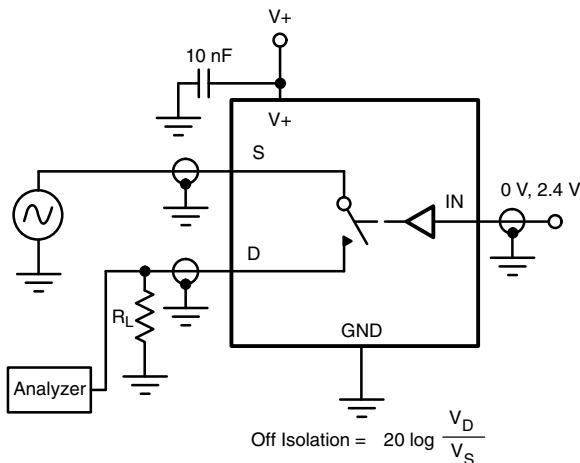


$V_{IN} = 0 - V+$



IN depends on switch configuration: input polarity determined by sense of switch.

Fig. 2 - Charge Injection



$$\text{Off Isolation} = 20 \log \frac{V_D}{V_S}$$

Fig. 3 - Off-Isolation

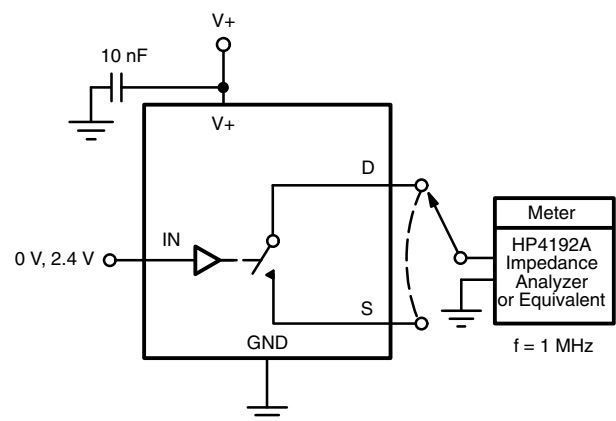


Fig. 4 - Channel Off/On Capacitance

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### QFN 4x4-16L Case Outline



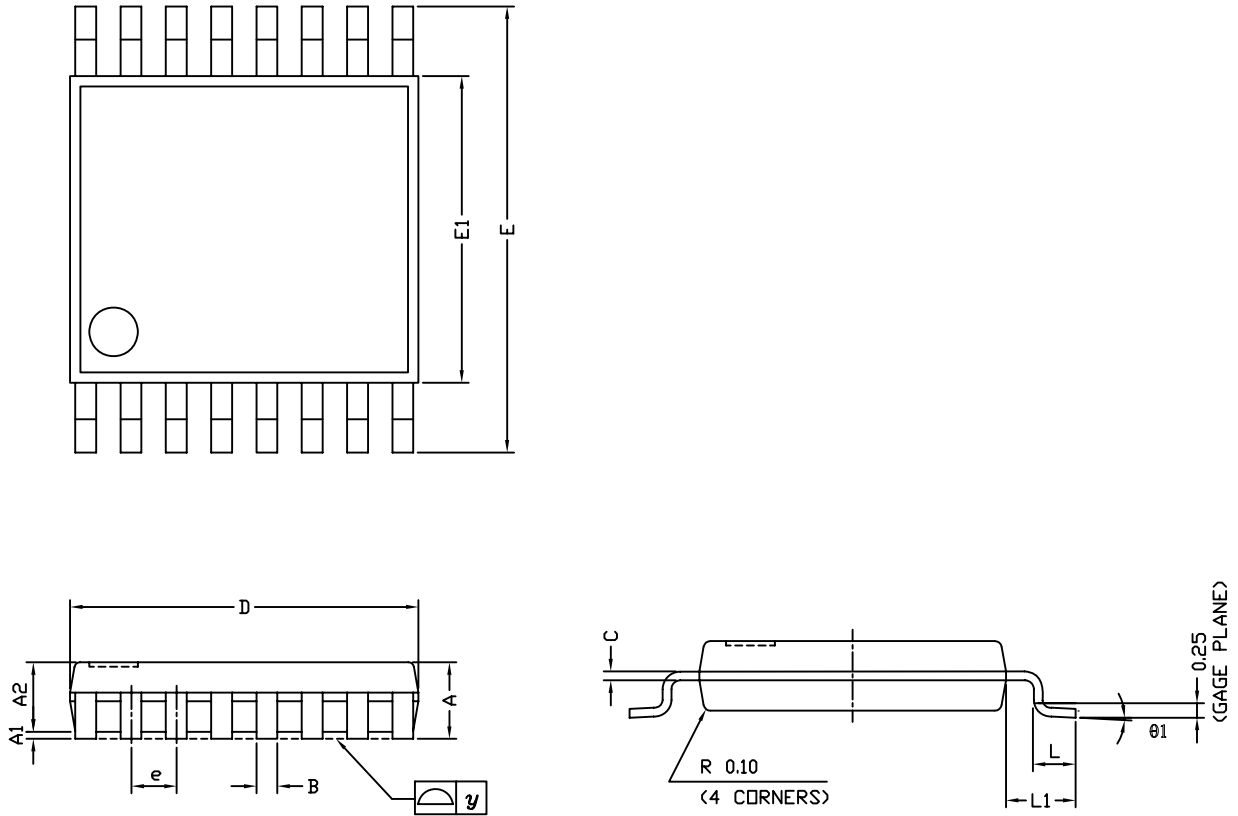
DIM	VARIATION 1						VARIATION 2					
	MILLIMETERS <sup>(1)</sup>			INCHES			MILLIMETERS <sup>(1)</sup>			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.75	0.85	0.95	0.029	0.033	0.037	0.75	0.85	0.95	0.029	0.033	0.037
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
A3	0.20 ref.			0.008 ref.			0.20 ref.			0.008 ref.		
b	0.25	0.30	0.35	0.010	0.012	0.014	0.25	0.30	0.35	0.010	0.012	0.014
D	4.00 BSC			0.157 BSC			4.00 BSC			0.157 BSC		
D2	2.0	2.1	2.2	0.079	0.083	0.087	2.5	2.6	2.7	0.098	0.102	0.106
e	0.65 BSC			0.026 BSC			0.65 BSC			0.026 BSC		
E	4.00 BSC			0.157 BSC			4.00 BSC			0.157 BSC		
E2	2.0	2.1	2.2	0.079	0.083	0.087	2.5	2.6	2.7	0.098	0.102	0.106
K	0.20 min.			0.008 min.			0.20 min.			0.008 min.		
L	0.5	0.6	0.7	0.020	0.024	0.028	0.3	0.4	0.5	0.012	0.016	0.020
N <sup>(3)</sup>	16			16			16			16		
Nd <sup>(3)</sup>	4			4			4			4		
Ne <sup>(3)</sup>	4			4			4			4		

#### Notes

- (1) Use millimeters as the primary measurement.
- (2) Dimensioning and tolerances conform to ASME Y14.5M. - 1994.
- (3) N is the number of terminals. Nd and Ne is the number of terminals in each D and E site respectively.
- (4) Dimensions b applies to plated terminal and is measured between 0.15 mm and 0.30 mm from terminal tip.
- (5) The pin 1 identifier must be existed on the top surface of the package by using identification mark or other feature of package body.
- (6) Package warpage max. 0.05 mm.

ECN: S13-0893-Rev. B, 22-Apr-13  
DWG: 5890

## TSSOP: 16-LEAD



Symbols	DIMENSIONS IN MILLIMETERS		
	Min	Nom	Max
A	-	1.10	1.20
A1	0.05	0.10	0.15
A2	-	1.00	1.05
B	0.22	0.28	0.38
C	-	0.127	-
D	4.90	5.00	5.10
E	6.10	6.40	6.70
E1	4.30	4.40	4.50
e	-	0.65	-
L	0.50	0.60	0.70
L1	0.90	1.00	1.10
y	-	-	0.10
θ1	0°	3°	6°

ECN: S-61920-Rev. D, 23-Oct-06  
DWG: 5624



## RECOMMENDED MINIMUM PAD FOR TSSOP-16



Recommended Minimum Pads  
Dimensions in inches (mm)



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